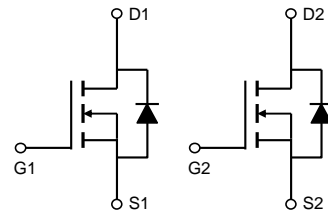


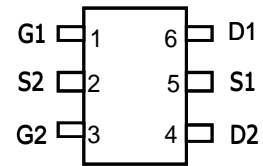
General Description

The AO6802 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.



Product Summary

- V_{DS} (V) = 30V
- $R_{DS(ON)} < 50m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 70 m\Omega$ ($V_{GS} = 4.5V$)



SOT23-6

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	3.5
		$T_A=70^\circ\text{C}$	3
Pulsed Drain Current ^C	I_{DM}	20	A
Power Dissipation ^B	P_D	$T_A=25^\circ\text{C}$	1.15
		$T_A=70^\circ\text{C}$	0.73
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	78	110	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		Steady-State	106	150
Maximum Junction-to-Lead	$R_{\theta JL}$	64	80	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.5	2	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3.5A		40	50	mΩ
		V _{GS} =4.5V, I _D =2A		52	70	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3.5A		12		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.79	1	V
I _S	Maximum Body-Diode Continuous Current				1.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		170	210	pF
C _{oss}	Output Capacitance			35		pF
C _{riss}	Reverse Transfer Capacitance			23		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.7	3.5	5.3	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =3.5A		4.05	5	nC
Q _g (4.5V)	Total Gate Charge			2	3	nC
Q _{gs}	Gate Source Charge			0.55		nC
Q _{gd}	Gate Drain Charge			1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =4.2Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			1.5		ns
t _{D(off)}	Turn-Off DelayTime			18.5		ns
t _f	Turn-Off Fall Time			15.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =3.5A, dI/dt=100A/μs		7.5	10	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3.5A, dI/dt=100A/μs		2.5		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

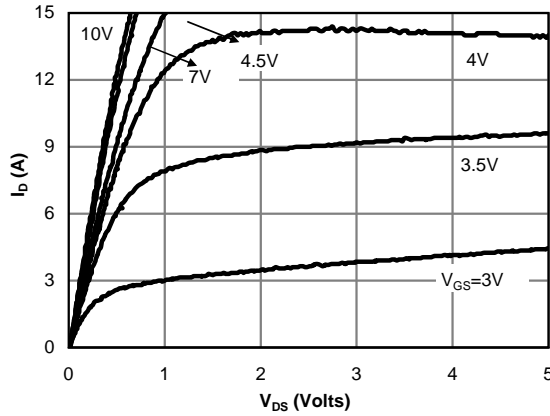


Figure 1: On-Region Characteristics (Note E)

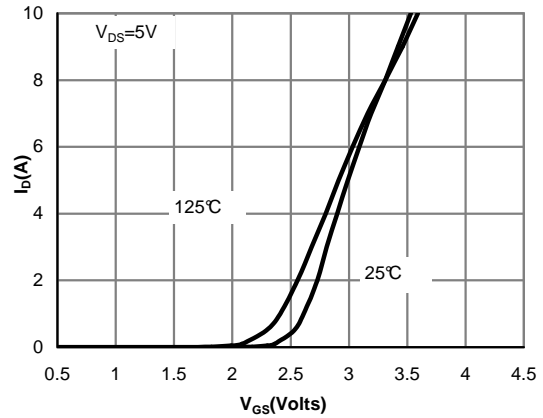


Figure 2: Transfer Characteristics (Note E)

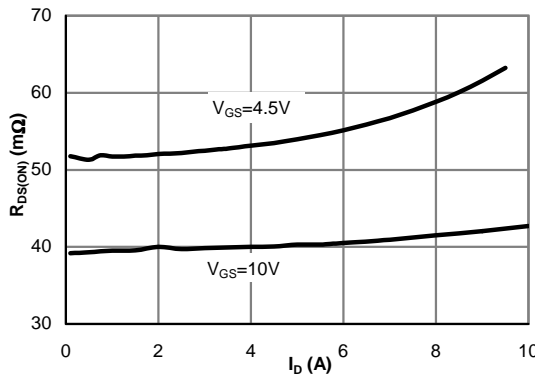


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

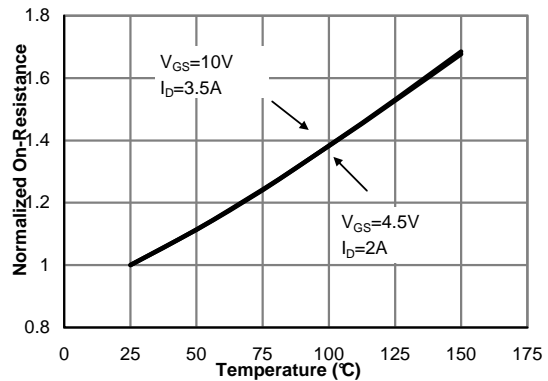


Figure 4: On-Resistance vs. Junction Temperature (Note E)

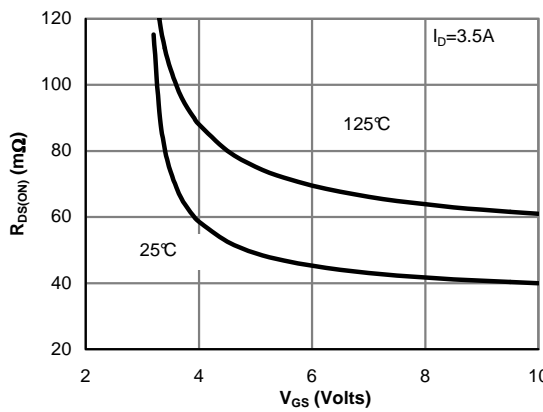


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

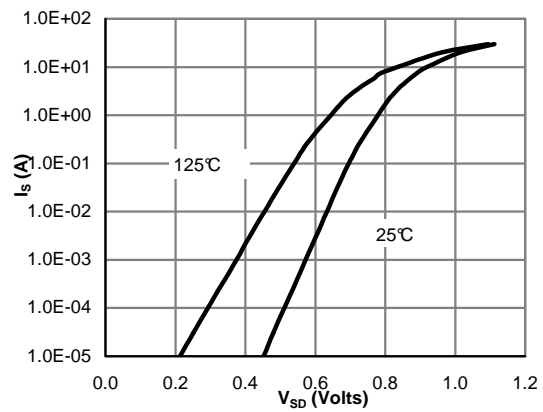


Figure 6: Body-Diode Characteristics (Note E)

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

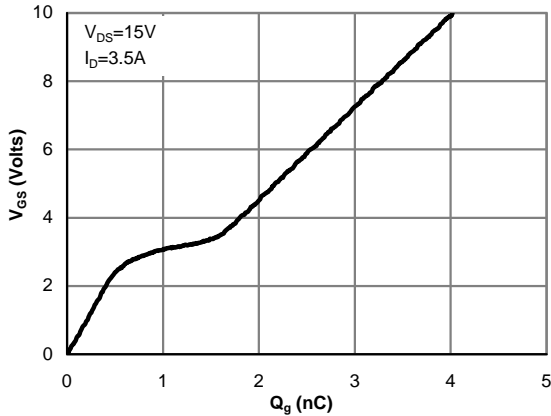


Figure 7: Gate-Charge Characteristics

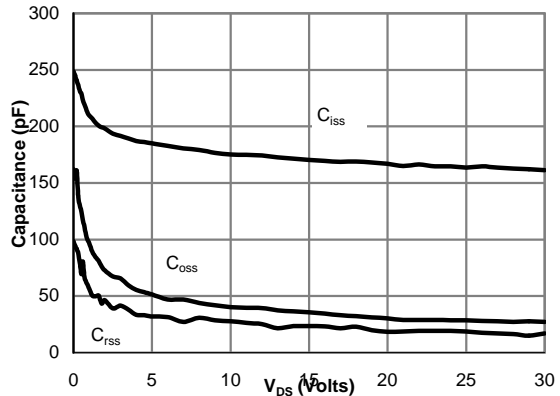


Figure 8: Capacitance Characteristics

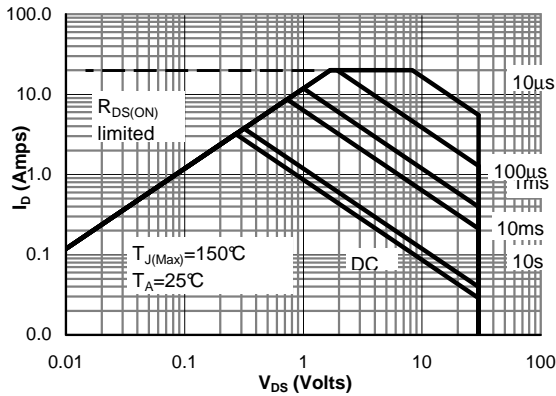


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

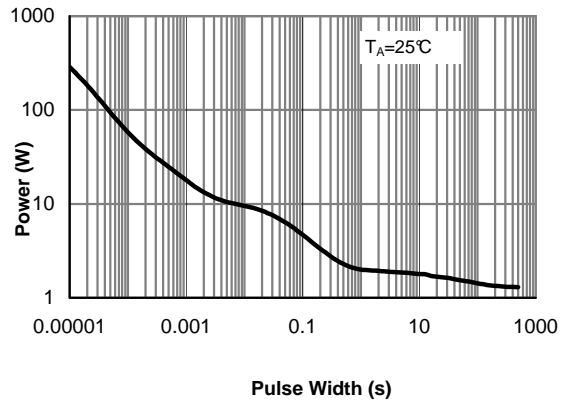


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

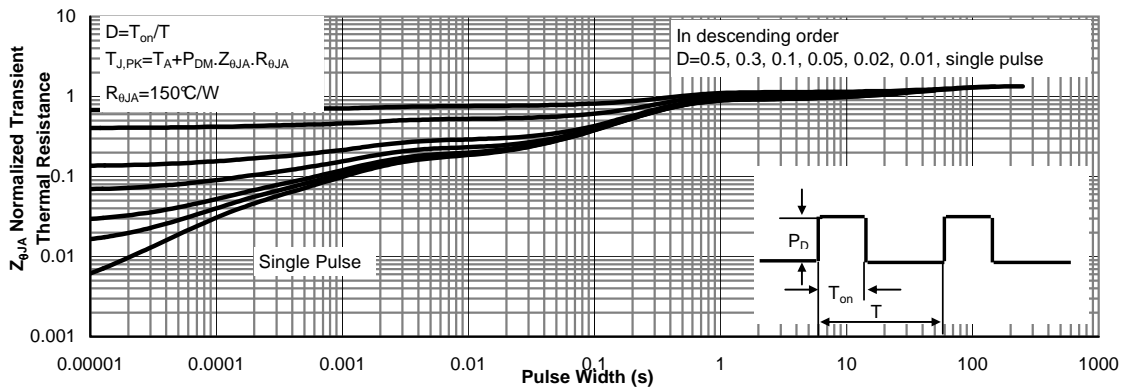
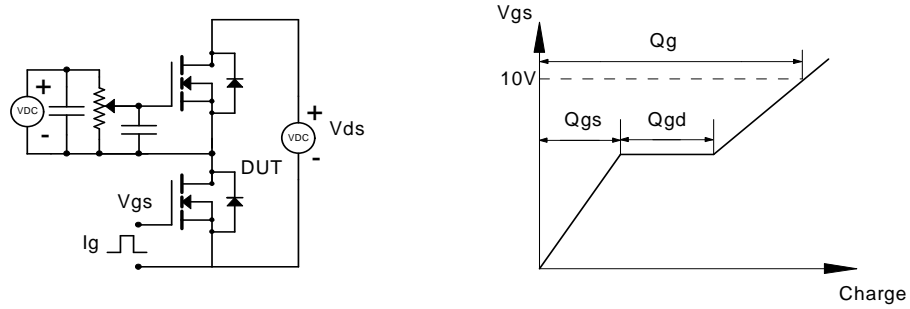
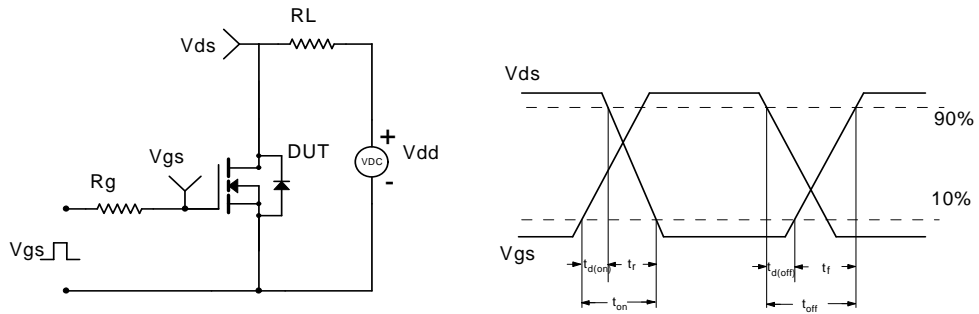


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

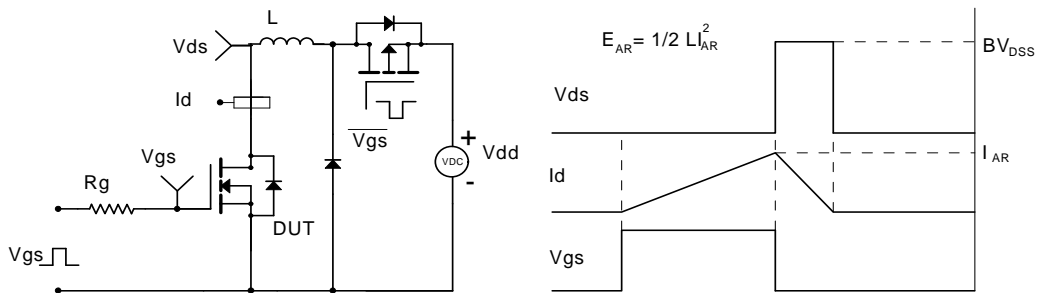
Gate Charge Test Circuit & Waveform



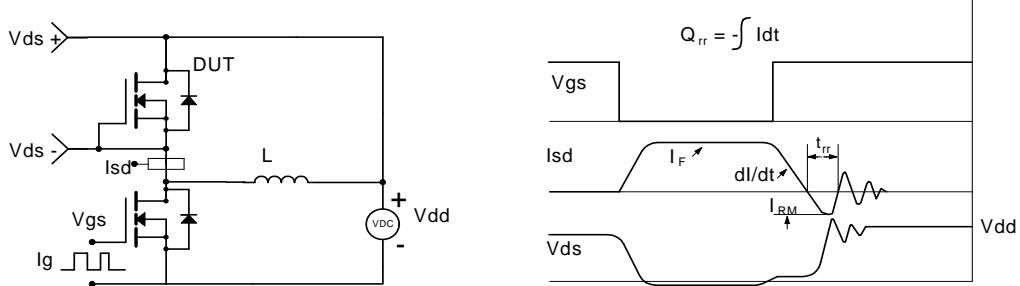
Resistive Switching Test Circuit & Waveforms



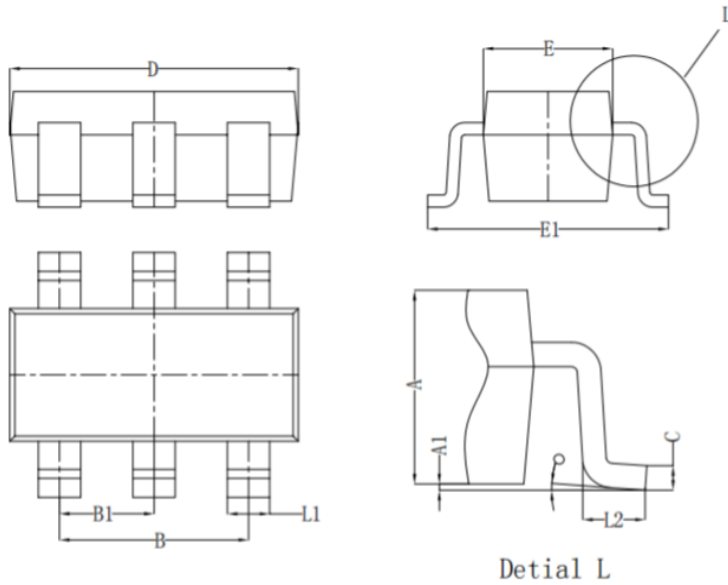
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



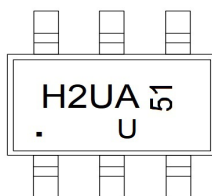
SOT23-6 PACKAGE OUTLIE DIMENSIONS



Detail L

Symbol	Dim in mm		
	Min	Nor	Max
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.300	0.450	0.600
o	0°	4°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
AO6802	SOT23-6	3000	Tape and reel